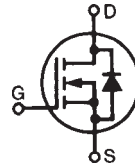


# Polar™ Power MOSFET

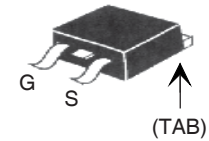
**IXTA2R4N120P**  
**IXTH2R4N120P**  
**IXTP2R4N120P**

**V<sub>DSS</sub> = 1200V**  
**I<sub>D25</sub> = 2.4A**  
**R<sub>DS(on)</sub> ≤ 7.5Ω**

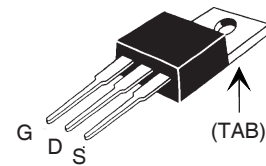
N-Channel Enhancement Mode  
Avalanche Rated



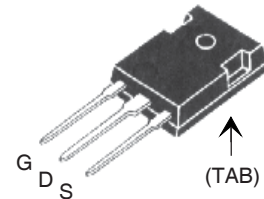
TO-263 (IXTA)



TO-220 (IXTP)



TO-247 (IXTH)



G = Gate      D = Drain  
S = Source    TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V <sub>DSS</sub>	T <sub>J</sub> = 25°C to 150°C	1200	V
V <sub>DGR</sub>	T <sub>J</sub> = 25°C to 150°C, R <sub>GS</sub> = 1MΩ	1200	V
V <sub>GSS</sub>	Continuous	±20	V
V <sub>GSM</sub>	Transient	±30	V
I <sub>D25</sub>	T <sub>C</sub> = 25°C	2.4	A
I <sub>DM</sub>	T <sub>C</sub> = 25°C, pulse width limited by T <sub>JM</sub>	6	A
I <sub>A</sub>	T <sub>C</sub> = 25°C	2.4	A
E <sub>AS</sub>	T <sub>C</sub> = 25°C	200	mJ
dV/dt	I <sub>S</sub> ≤ I <sub>DM</sub> , V <sub>DD</sub> ≤ V <sub>DSS</sub> , T <sub>J</sub> ≤ 150°C	10	V/ns
P <sub>D</sub>	T <sub>C</sub> = 25°C	125	W
T <sub>J</sub>		-55 ... +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 ... +150	°C
T <sub>L</sub>	1.6mm (0.062) from case for 10s	300	°C
T <sub>SOLD</sub>	Plastic body for 10s	260	°C
M <sub>d</sub>	Mounting torque (TO-220, TO-247)	1.13 / 10	Nm/lb.in.
Weight	TO-263	2.5	g
	TO-220	3.0	g
	TO-247	6.0	g

## Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect

## Advantages

- Easy to mount
- Space savings
- High power density

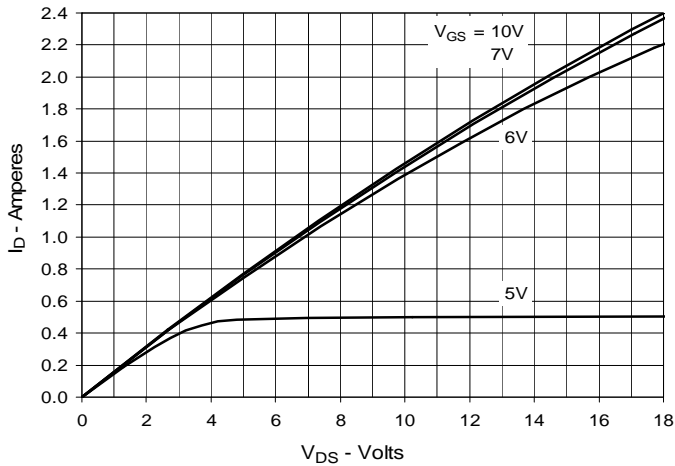
## Applications:

- High Voltage Switched-mode and resonant-mode power supplies
- High Voltage Pulse Power Applications
- High Voltage Discharge circuits in Lasers Pulsers, Spark Igniters, RF Generators
- High Voltage DC-DC converters
- High Voltage DC-AC inverters

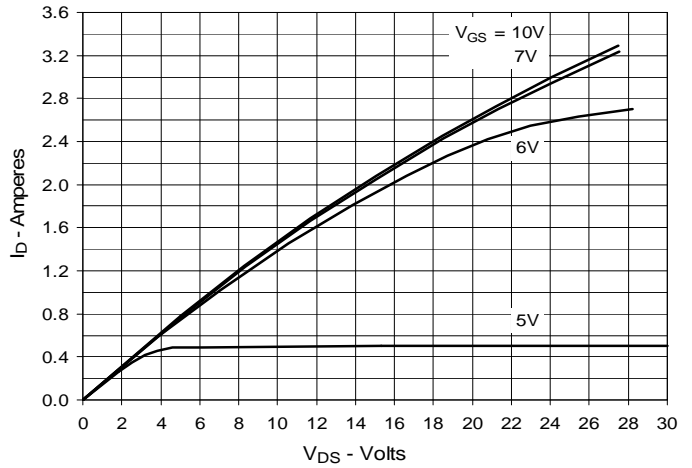
Symbol	Test Conditions (T <sub>J</sub> = 25°C, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	1200		V
V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2.5		4.5 V
I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±50 nA
I <sub>DSS</sub>	V <sub>DS</sub> = V <sub>DSS</sub> V <sub>GS</sub> = 0V      T <sub>J</sub> = 125°C			5 μA
				300 μA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.5 • I <sub>D25</sub> , Note 1	6.5	7.5	Ω



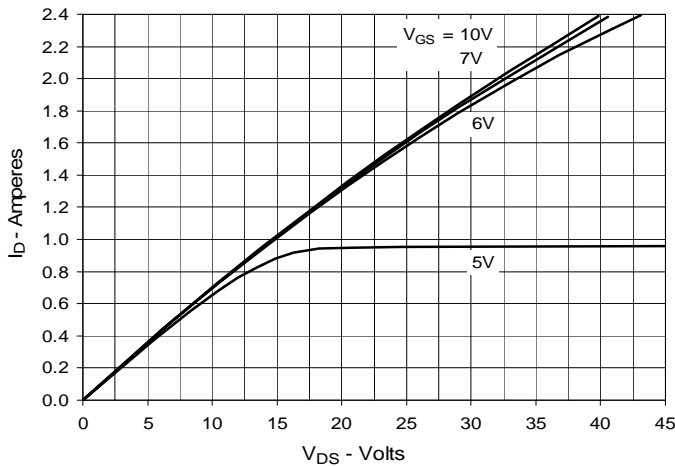
**Fig. 1. Output Characteristics @ 25°C**



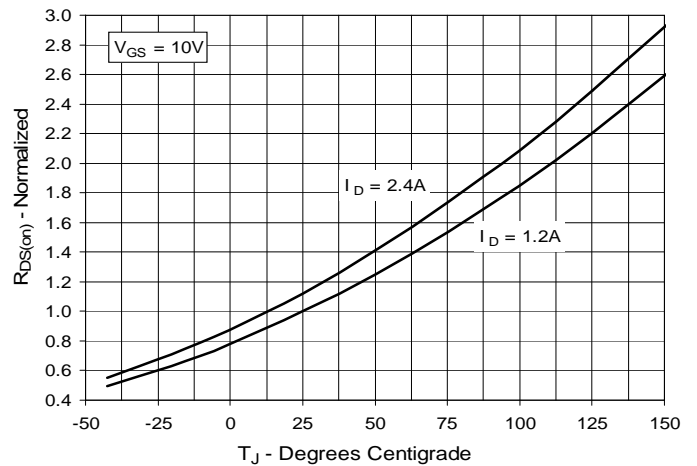
**Fig. 2. Extended Output Characteristics @ 25°C**



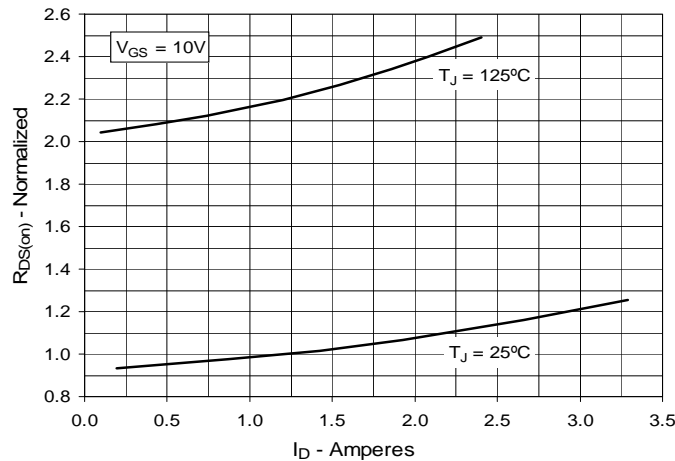
**Fig. 3. Output Characteristics @ 125°C**



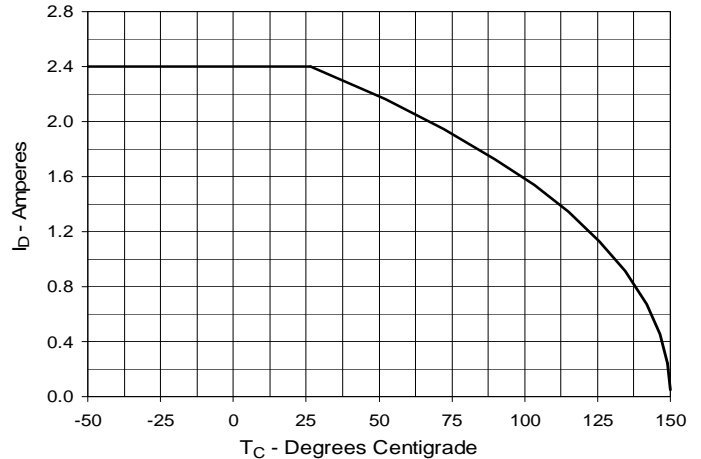
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 1.2A$  Value vs. Junction Temperature**



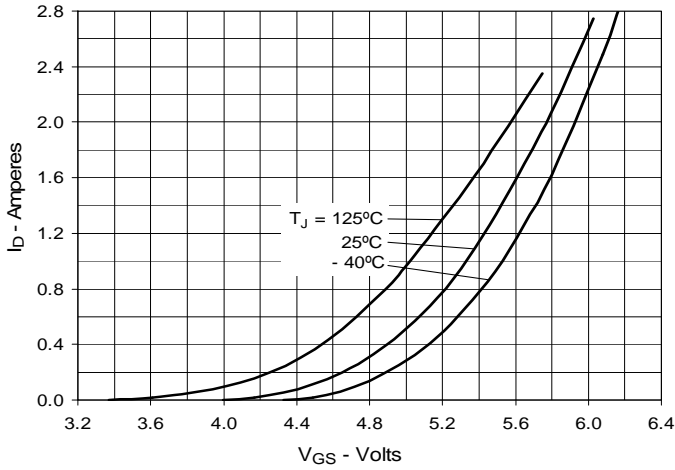
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 1.2A$  Value vs. Drain Current**



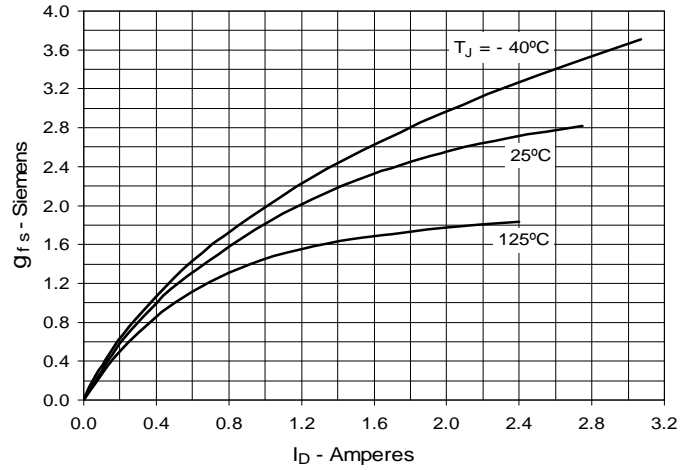
**Fig. 6. Maximum Drain Current vs. Case Temperature**



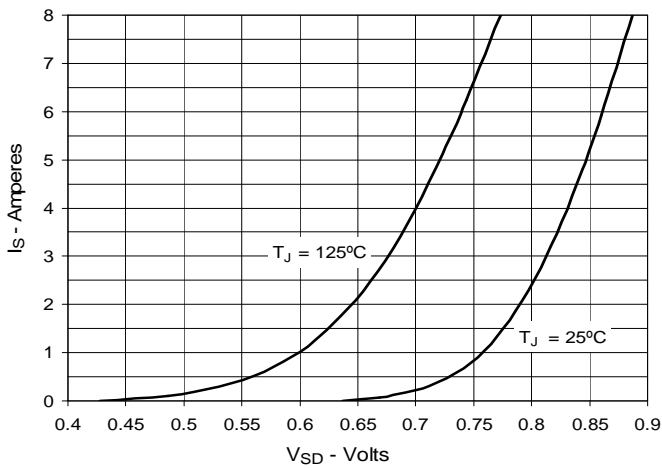
**Fig. 7. Input Admittance**



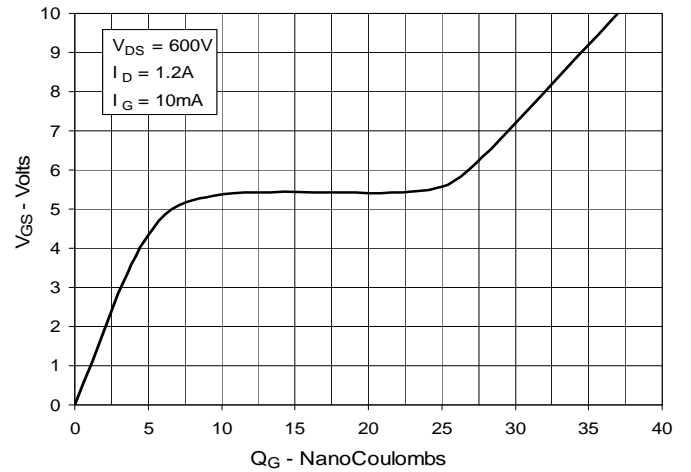
**Fig. 8. Transconductance**



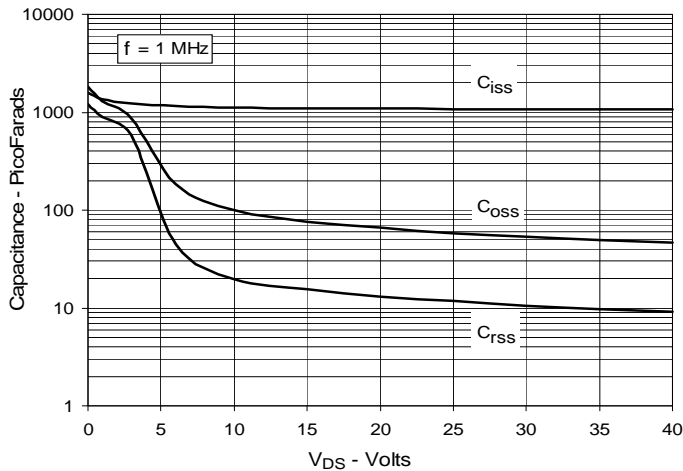
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



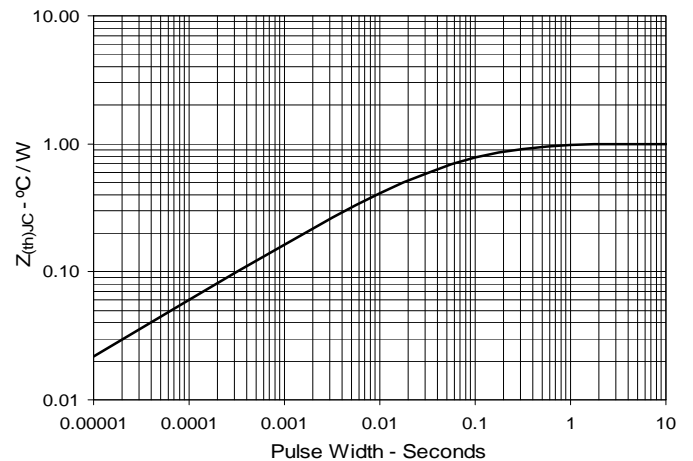
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Impedance**



IXYS reserves the right to change limits, test conditions, and dimensions.